

In the Specification:

Please amend paragraph 0010 of the Specification as follows:

[0010] In another preferred embodiment of a method according to the invention, the first and second implantations (I_1 , I_2) are annealed at a temperature between 500 ~~[[en]]~~ and 700 degrees Celsius. In this way, both the horizontal and the vertical part of the pn-junction are formed by solid phase epitaxial regrowth. This greatly contributes to the shallowness and steepness of the pn-junction formed, which in turn is essential for future C-MOS technology.